International
IOR Rectifier

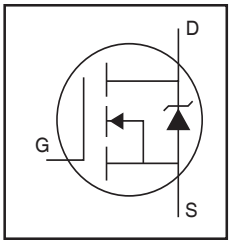
**AUTOMOTIVE GRADE**

# AUIRF2805

HEXFET® Power MOSFET

### Features

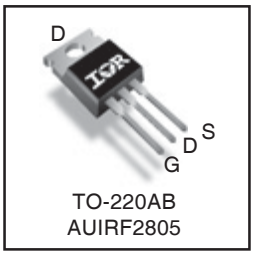
- Advanced Planar Technology
- Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*




| | |
|---|---|
| $V_{(BR)DSS}$ | 55V |
| $R_{DS(on)}$ typ. | 3.9mΩ |
| max | 4.7mΩ |
| $I_{D\ (Silicon\ Limited)}$ | 175A |
| $I_{D\ (Package\ Limited)}$ | 75A |

### Description

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.




TO-220AB
AUIRF2805

| G | D | S |
|---|---|---|
| Gate | Drain | Source |

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ($T_A$) is 25°C, unless otherwise specified.

| | Parameter | Max. | Units |
|---|---|---|---|
| $I_D$ @ $T_C$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 10V (Silicon Limited) | 175 | A |
| $I_D$ @ $T_C$ = 100°C | Continuous Drain Current, VGS @ 10V (Silicon Limited) | 120 | |
| $I_D$ @ $T_C$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 10V (Package Limited) | 75 | |
| $I_{DM}$ | Pulsed Drain Current ① | 700 | |
| $P_D$ @$T_C$ = 25°C | Power Dissipation | 330 | W |
| | Linear Derating Factor | 2.2 | W/°C |
| $V_{GS}$ | Gate-to-Source Voltage | ± 20 | V |
| $E_{AS}$ | Single Pulse Avalanche Energy (Thermally Limited)② | 450 | mJ |
| $E_{AS}$ (tested) | Single Pulse Avalanche Energy Tested Value ⑦ | 1220 | |
| $I_{AR}$ | Avalanche Current ① | See Fig. 12a, 12b, 15, 16 | A |
| $E_{AR}$ | Repetitive Avalanche Energy ⑥ | | mJ |
| $T_J$ | Operating Junction and | -55 to + 175 | °C |
| $T_{STG}$ | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds (1.6mm from case ) | 300 | |
| | Mounting Torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

## Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|---|---|---|---|---|
| $R_{\theta JC}$ | Junction-to-Case ⑧ | — | 0.45 | °C/W |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 62 | |

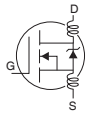
HEXFET® is a registered trademark of International Rectifier.
*Qualification standards can be found at http://www.irf.com/

## Static Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 55 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250µA |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.06 | — | V/°C | Reference to 25°C, $I_D$ = 1mA |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | 3.9 | 4.7 | mΩ | $V_{GS}$ = 10V, $I_D$ = 104A ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 2.0 | — | 4.0 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| gfs | Forward Transconductance | 91 | — | — | S | $V_{DS}$ = 25V, $I_D$ = 104A |
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | 20 | µA | $V_{DS}$ = 55V, $V_{GS}$ = 0V |
| | | — | — | 250 | | $V_{DS}$ = 55V, $V_{GS}$ = 0V, $T_J$ = 125°C |
| $I_{GSS}$ | Gate-to-Source Forward Leakage | — | — | 200 | nA | $V_{GS}$ = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | $V_{GS}$ = -20V |

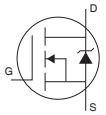
## Dynamic Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $Q_g$ | Total Gate Charge | — | 150 | 230 | | $I_D$ = 104A |
| $Q_{gs}$ | Gate-to-Source Charge | — | 38 | 57 | nC | $V_{DS}$ = 44V |
| $Q_{gd}$ | Gate-to-Drain ("Miller") Charge | — | 52 | 78 | | $V_{GS}$ = 10V ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 14 | — | | $V_{DD}$ = 28V |
| $t_r$ | Rise Time | — | 120 | — | | $I_D$ = 104A |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 68 | — | ns | $R_G$ = 2.5 Ω |
| $t_f$ | Fall Time | — | 110 | — | | $V_{GS}$ = 10V ④ |
| $L_D$ | Internal Drain Inductance | — | 4.5 | — | | Between lead, |
| | | | | | nH | 6mm (0.25in.) |
| $L_S$ | Internal Source Inductance | — | 7.5 | — | | from package |
| | | | | | | and center of die contact |
| $C_{iss}$ | Input Capacitance | — | 5110 | — | | $V_{GS}$ = 0V |
| $C_{oss}$ | Output Capacitance | — | 1190 | — | pF | $V_{DS}$ = 25V |
| $C_{rss}$ | Reverse Transfer Capacitance | — | 210 | — | | $f$ = 1.0MHz, See Fig. 5 |
| $C_{oss}$ | Output Capacitance | — | 6470 | — | | $V_{GS}$ = 0V, $V_{DS}$ = 1.0V, $f$ = 1.0MHz |
| $C_{oss}$ | Output Capacitance | — | 860 | — | | $V_{GS}$ = 0V, $V_{DS}$ = 44V, $f$ = 1.0MHz |
| $C_{oss}$ eff. | Effective Output Capacitance ⑤ | — | 1600 | — | | $V_{GS}$ = 0V, $V_{DS}$ = 0V to 44V |




## Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current | — | — | 175 | | MOSFET symbol |
| | (Body Diode) | | | | A | showing the |
| $I_{SM}$ | Pulsed Source Current | — | — | 700 | | integral reverse |
| | (Body Diode) ① | | | | | p-n junction diode. |
| $V_{SD}$ | Diode Forward Voltage | — | — | 1.3 | V | $T_J$ = 25°C, $I_S$ = 104A, $V_{GS}$ = 0V ④ |
| $t_{rr}$ | Reverse Recovery Time | — | 80 | 120 | ns | $T_J$ = 25°C, $I_F$ = 104A |
| $Q_{rr}$ | Reverse Recovery Charge | — | 290 | 430 | nC | di/dt = 100A/µs ④ |
| $t_{on}$ | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |




**Notes:**

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).

② Starting $T_J$ = 25°C, L = 0.08mH $R_G$ = 25Ω, $I_{AS}$ = 104A. (See Figure 12).

③ $I_{SD}$ ≤ 104A, di/dt ≤ 240A/µs, $V_{DD}$ ≤ $V_{(BR)DSS}$, $T_J$ ≤ 175°C

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

⑤ $C_{oss}$ eff. is a fixed capacitance that gives the same charging time as $C_{oss}$ while $V_{DS}$ is rising from 0 to 80% $V_{DSS}$ .

⑥ Limited by $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.

⑦ This value determined from sample failure population, starting $T_J$ = 25°C, L = 0.08mH, $R_G$ = 25Ω, $I_{AS}$ = 104A.

⑧ $R_\theta$ is measured at $T_J$ of approximately 90°C.

**Qualification Information**†

| | | | |
|---|---|---|---|
| **Qualification Level** | | Automotive (per AEC-Q101) †† | |
| | | Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| **Moisture Sensitivity Level** | | TO-220 | N/A |
| **ESD** | Machine Model | Class M4 (+/- >800V)††† AEC-Q101-002 | |
| | Human Body Model | Class H3A (+/- 5000V)††† AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- >2000V)††† AEC-Q101-005 | |
| **RoHS Compliant** | | Yes | |

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

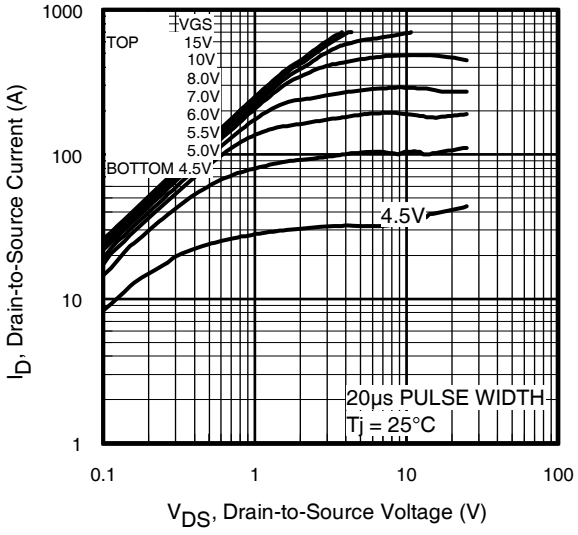



**Fig 1.** Typical Output Characteristics

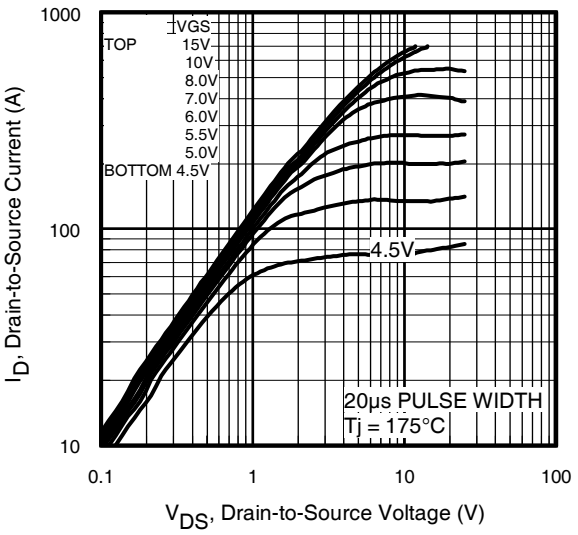



**Fig 2.** Typical Output Characteristics

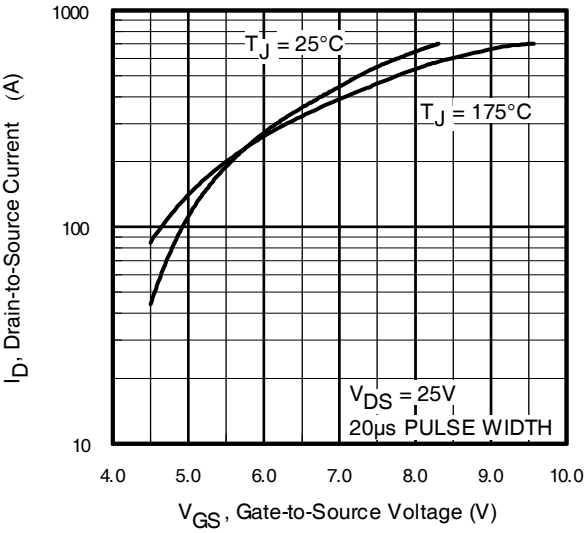



**Fig 3.** Typical Transfer Characteristics

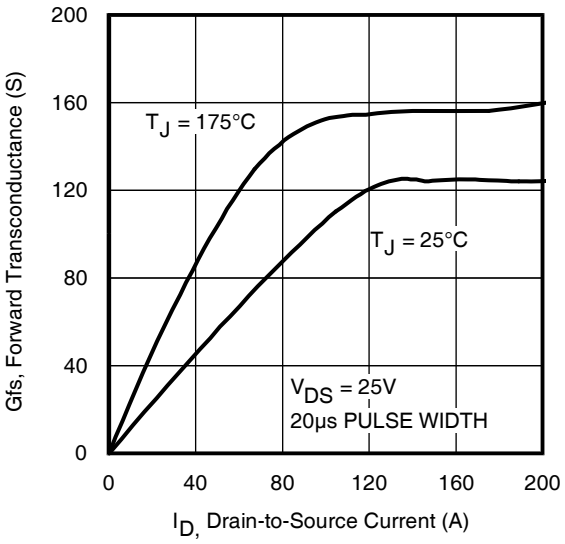



**Fig 4.** Typical Forward Transconductance Vs. Drain Current

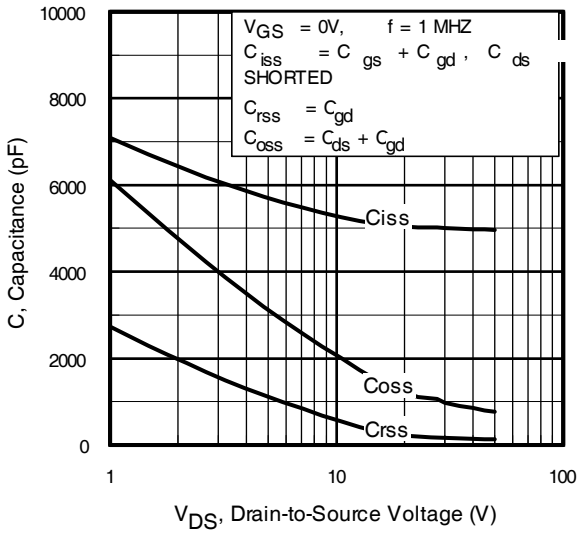



**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage

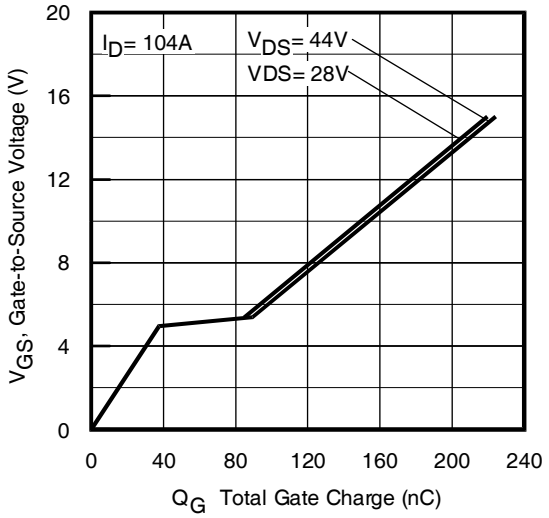



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

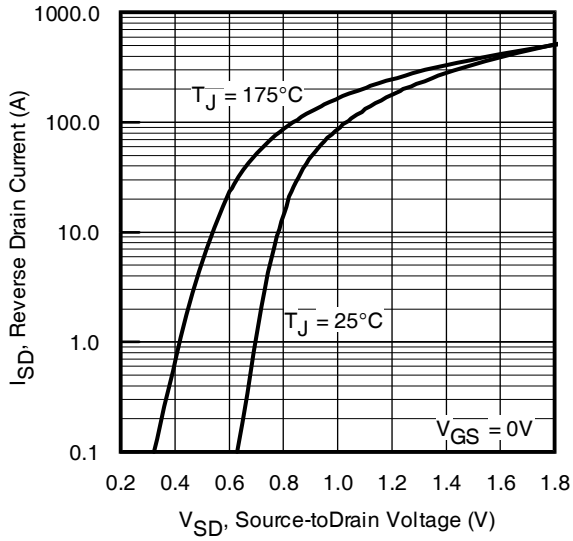



**Fig 7.** Typical Source-Drain Diode Forward Voltage

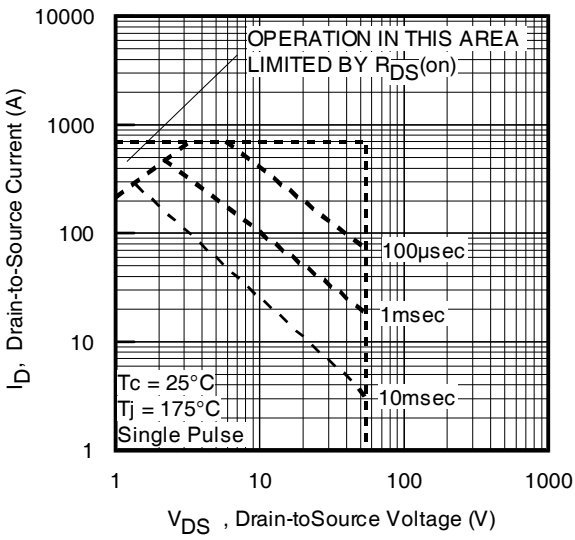



**Fig 8.** Maximum Safe Operating Area

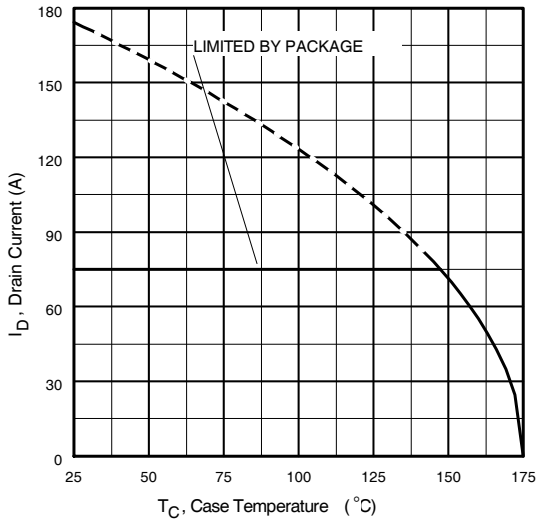



**Fig 9.** Maximum Drain Current Vs. Case Temperature

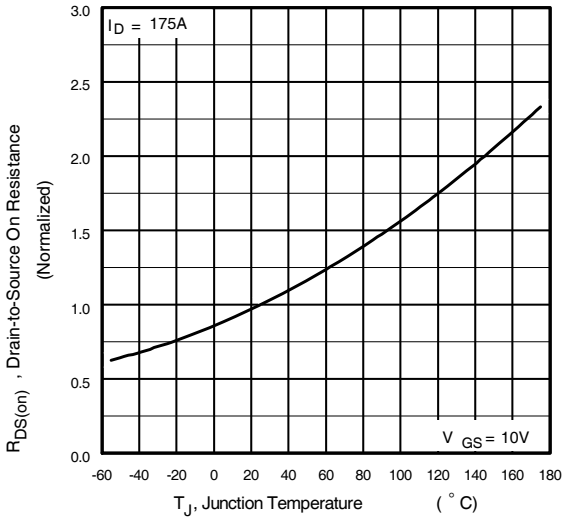



**Fig 10.** Normalized On-Resistance Vs. Temperature

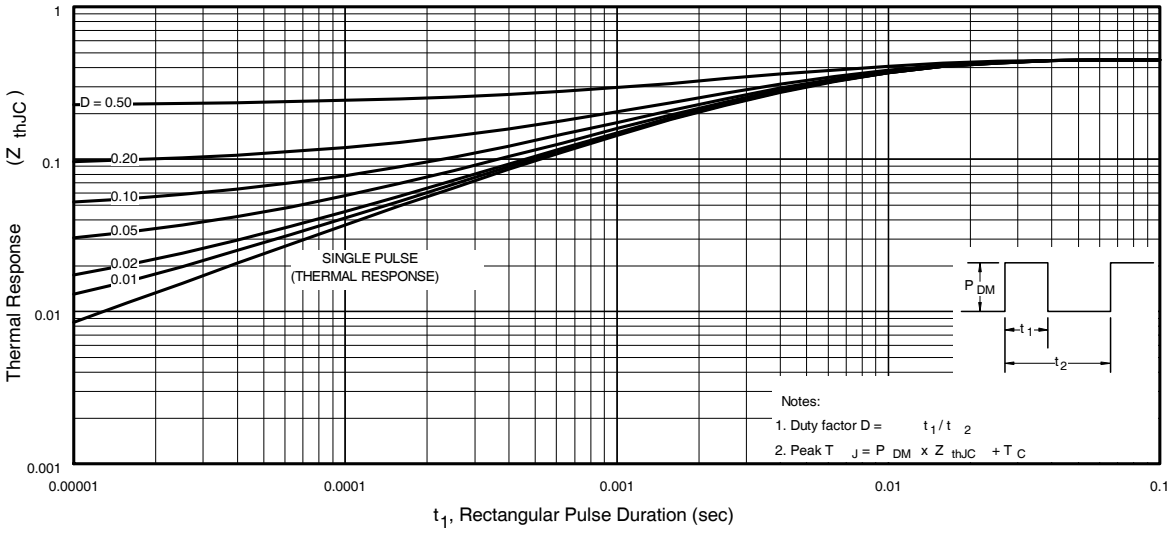



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

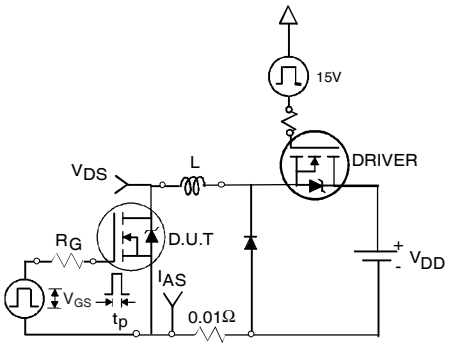



**Fig 12a.** Unclamped Inductive Test Circuit

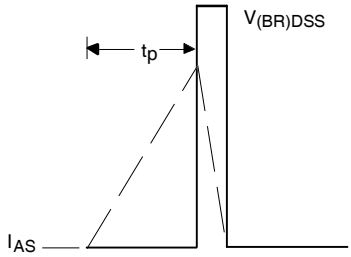



**Fig 12b.** Unclamped Inductive Waveforms

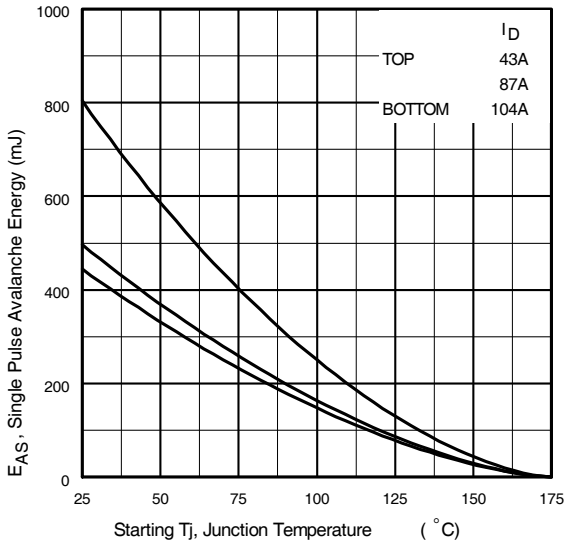



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

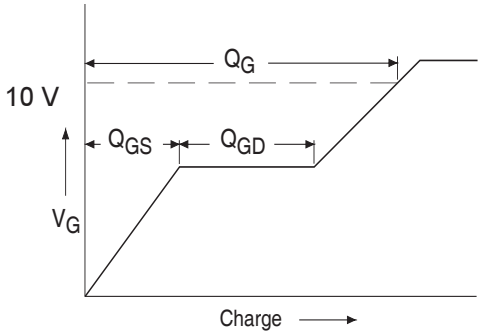



**Fig 13a.** Basic Gate Charge Waveform

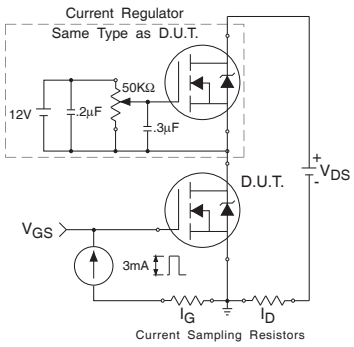



**Fig 13b.** Gate Charge Test Circuit

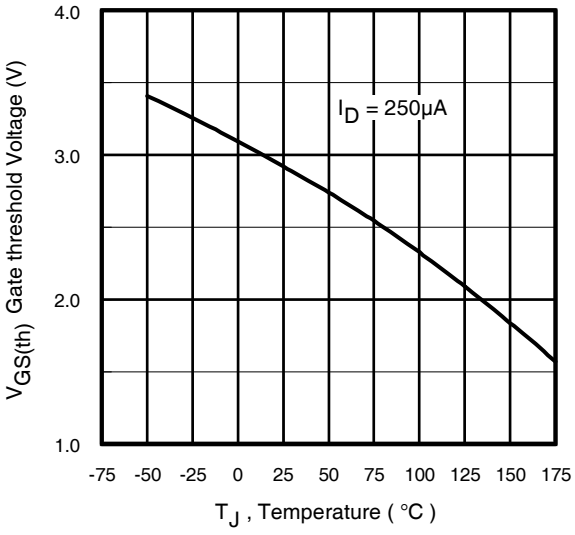



**Fig 14.** Threshold Voltage Vs. Temperature

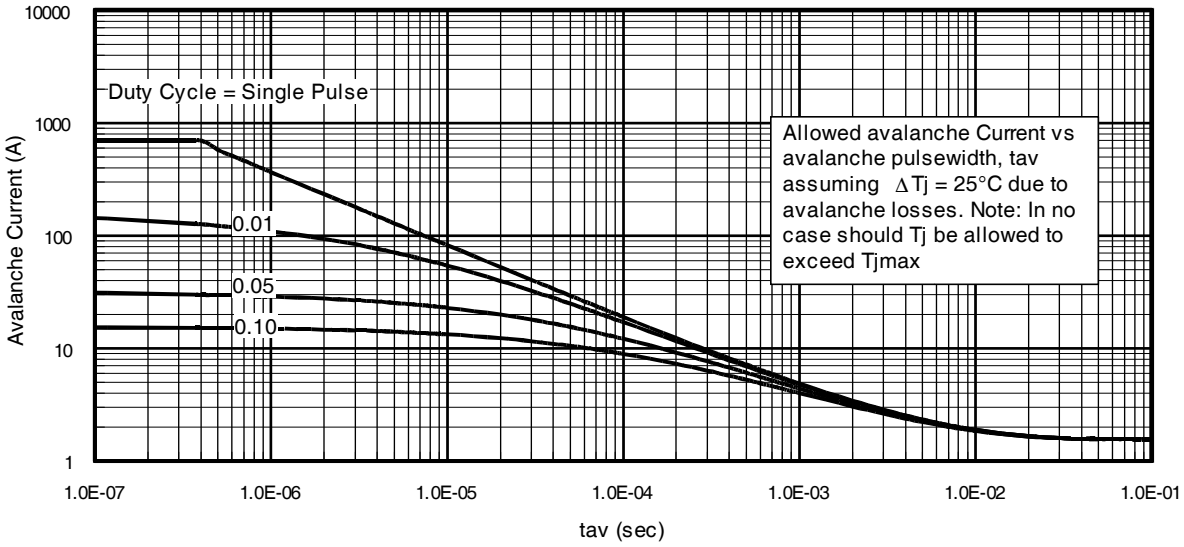



**Fig 15.** Typical Avalanche Current Vs.Pulsewidth

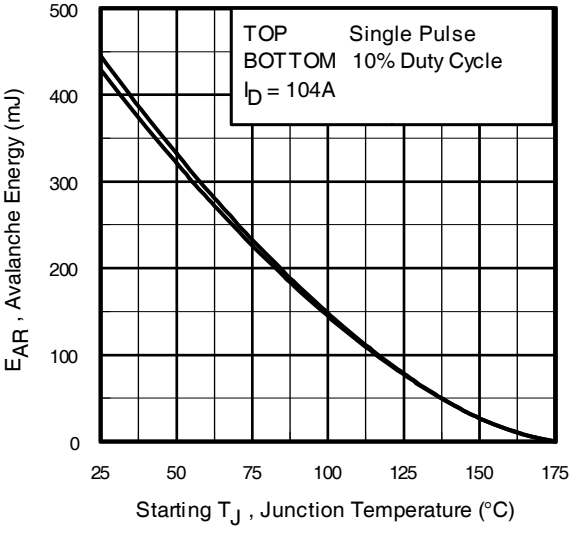



**Fig 16.** Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16: (For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption: Purely a thermal phenomenon and failure occurs at a temperature far in excess of $T_{jmax}$. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as$T_{jmax}$ is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. $I_{av}$ = Allowable avalanche current.
7. $\Delta T$ = Allowable rise in junction temperature, not to exceed $T_{jmax}$ (assumed as 25°C in Figure 15, 16).
   $t_{av}$ = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D\ (ave)} = 1/2\ (\ 1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

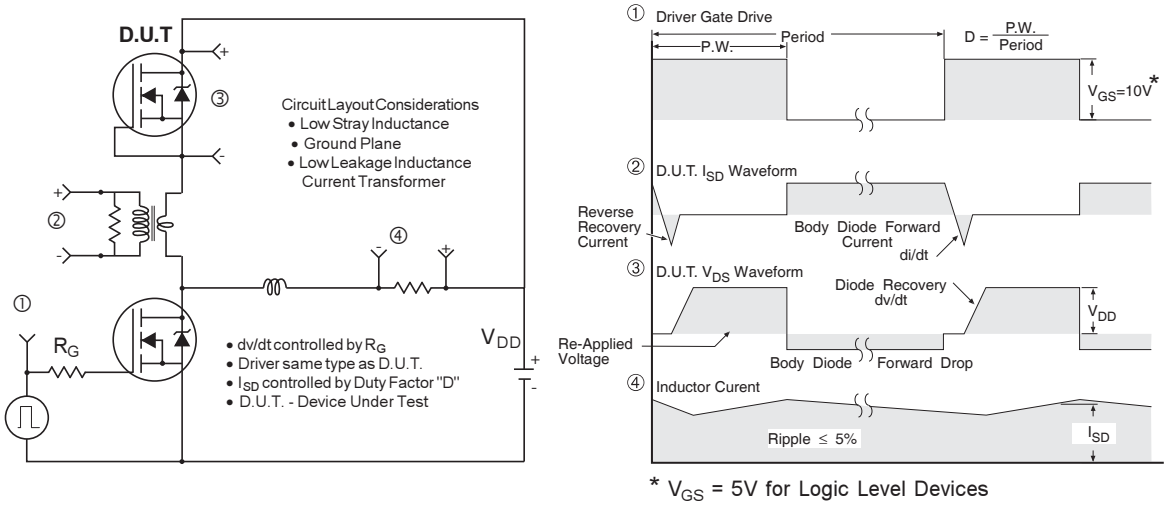



**Fig 17.** Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

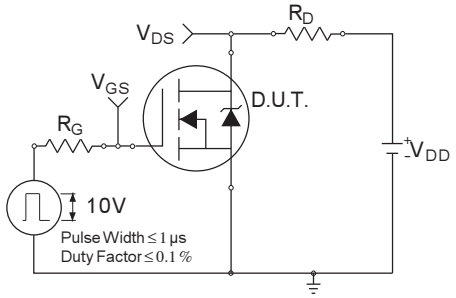



**Fig 18a.** Switching Time Test Circuit

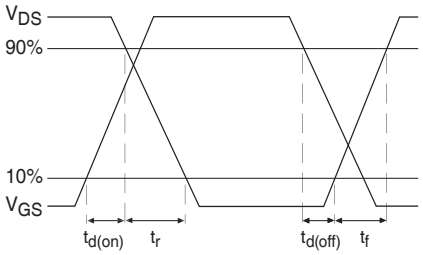
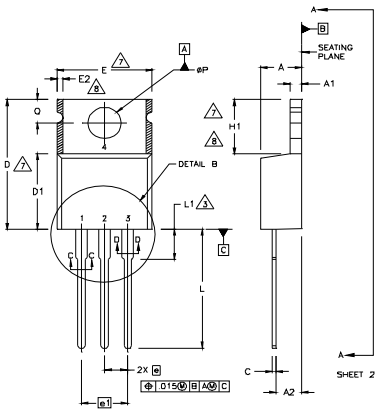
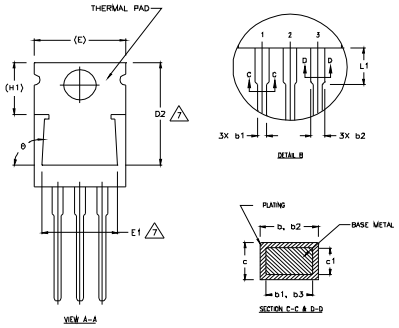



**Fig 18b.** Switching Time Waveforms

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)




NOTES:

1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6 CONTROLLING DIMENSION : INCHES.
7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

| SYMBOL | DIMENSIONS | | | | NOTES |
|---|---|---|---|---|---|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 3.56 | 4.82 | .140 | .190 | |
| A1 | 0.51 | 1.40 | .020 | .055 | |
| A2 | 2.04 | 2.92 | .080 | .115 | |
| b | 0.38 | 1.01 | .015 | .040 | |
| b1 | 0.38 | 0.96 | .015 | .038 | 5 |
| b2 | 1.15 | 1.77 | .045 | .070 | |
| b3 | 1.15 | 1.73 | .045 | .068 | |
| c | 0.36 | 0.61 | .014 | .024 | |
| c1 | 0.36 | 0.56 | .014 | .022 | 5 |
| D | 14.22 | 16.51 | .560 | .650 | 4 |
| D1 | 8.38 | 9.02 | .330 | .355 | |
| D2 | 12.19 | 12.88 | .480 | .507 | 7 |
| E | 9.66 | 10.66 | .380 | .420 | 4,7 |
| E1 | 8.38 | 8.89 | .330 | .350 | 7 |
| e | 2.54 BSC | | .100 BSC | | |
| e1 | 5.08 | | .200 BSC | | |
| H1 | 5.85 | 6.55 | .230 | .270 | 7,8 |
| L | 12.70 | 14.73 | .500 | .580 | |
| L1 | – | 6.35 | – | .250 | 3 |
| øP | 3.54 | 4.08 | .139 | .161 | |
| Q | 2.54 | 3.42 | .100 | .135 | |
| ø | 90°-93° | | 90°-93° | | |

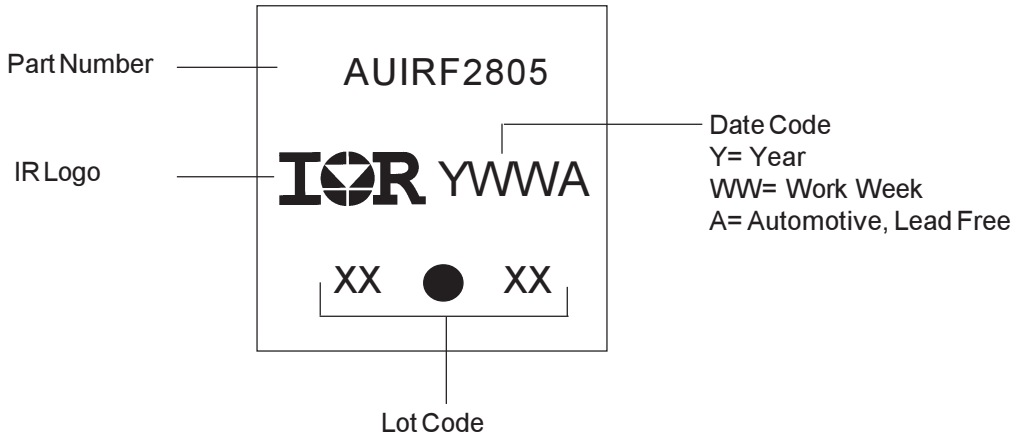
LEAD ASSIGNMENTS

HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK
1.- GATE
2.- COLLECTOR
3.- EMITTER

DIODES
1.- ANODE/OPEN
2.- CATHODE
3.- ANODE

## TO-220AB Part Marking Information




**Note: For the most current drawing please refer to IR website at http://www.irf.com/package/**

## Ordering Information

| Base part number | Package Type | Standard Pack | | Complete Part Number |
|---|---|---|---|---|
| | | Form | Quantity | |
| AUIRF2805 | TO-220 | Tube | 50 | AUIRF2805 |

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